RECTRON SEMICONDUCTOR TECHNICAL SPECIFICATION

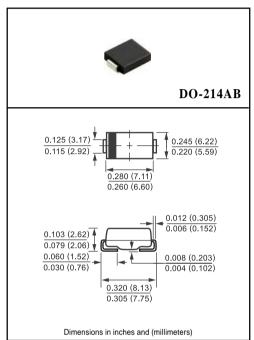


SURFACE MOUNT GLASS PASSIVATED HIGH EFFICIENCY SILICON RECTIFIER

VOLTAGE RANGE 50 to 1000 Volts CURRENT 3.0 Amperes

FEATURES

- * Glass passivated device
- * Ideal for surface mounted applications
- * Low leakage current
- * Metallurgically bonded construction
- * Mounting position: Any
- * Weight: 0.24 gram



Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.

MAXIMUM RATINGS (At TA = 25°C unless otherwise noted)

RATINGS	SYMBOL	HFM301	HFM302	HFM303	HFM304	HFM305	HFM306	HFM307	HFM308	UNITS
Maximum Recurrent Peak Reverse Voltage	VRRM	50	100	200	300	400	600	800	1000	Volts
Maximum RMS Volts	VRMS	35	70	140	210	280	420	560	700	Volts
Maximum DC Blocking Voltage	VDC	50	100	200	300	400	600	800	1000	Volts
Maximum Average Forward Current at TA = 50° C	lo	3.0								Amps
Peak Forward Surge Current 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	IFSM	200					150			Amps
Typical Junction Capacitance (Note 2)	Cu	70					50			pF
Operating and Storage Temperature Range	TJ, TSTG	-65 to + 175								°C

ELECTRICAL CHARACTERISTICS (At TA = 25°C unless otherwise noted)

CHARACTERISTICS		SYMBOL	HFM301 H	HFM302	HFM303	HFM304	HFM305	HFM306	HFM307	HFM308	UNITS
Maximum Forward Voltage at 3.0A DC		VF	1.0		1.	3	1.7			Volts	
Maximum Full Load Reverse Current, Full cycle Average TA=55°C				50							
Maximum DC Reverse Current at	@TA = 25°C	IR	10								uAmps
Rated DC Blocking Voltage	@TA = 125°C		150								uAmps
Maximum Reverse Recovery Time (Note 1)		trr	50					75		nSec	

NOTES: 1. Test Conditions: IF=0.5A, IR=1.0A, IRR=0.25A.

2. Measured at 1 MHz and applied reverse voltage of 4.0 volts.

RATING AND CHARACTERISTIC CURVES (HFM301 THRU HFM306)

